Toshiba Intelligent Power Device Silicon Monolithic Power MOS Integrated Circuit

TPD1036F

2-IN-1 Low-Side Power Switch for Motor, Solenoid and Lamp Drivers

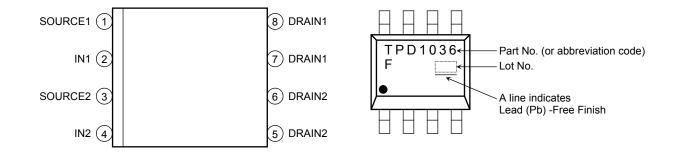
The TPD1036F is a 2-IN-1 low-side switch. The output has a vertical MOSFET, and the input can be directly driven from CMOS or TTL logic (e.g., an MPU). The IC provides intelligent protection functions.

Features

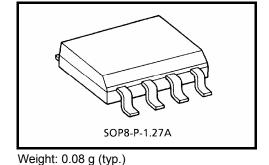
- Two built-in power IC chips with a structure that incorporates a control block and a vertical power MOSFET on each chip.
- Can be directly driven from a microprocessor, a CMOS logic IC, etc.
- Overvoltage (active clamp), overtemperature (thermal shutdown), and overcurrent (current limiter) protections are built in.
- Low ON-resistance: R_{DS} (ON) = 0.5 Ω (max) (@VIN = 5 V, ID = 0.7 A, T_{ch} = 25°C)
- Low drain cut-off current: $I_{DSS} = 10 \ \mu A \ (max) \ (@V_{IN} = 0 \ V, V_{DS} = 30 \ V, T_{ch} = 25^{\circ}C)$
- Low input current: $I_{IN} = 300 \ \mu A \ (max) \ (@V_{IN} = 5 \ V, T_{ch} = -40 \ to \ 110^{\circ}C)$
- Housed in the 8-pin SOP package and supplied in embossed carrier tape.

Pin Assignment (top view)

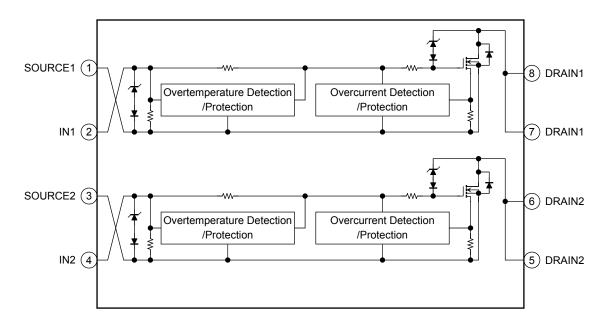
Marking



Note: This product has a MOS structure and is sensitive to electrostatic discharge.



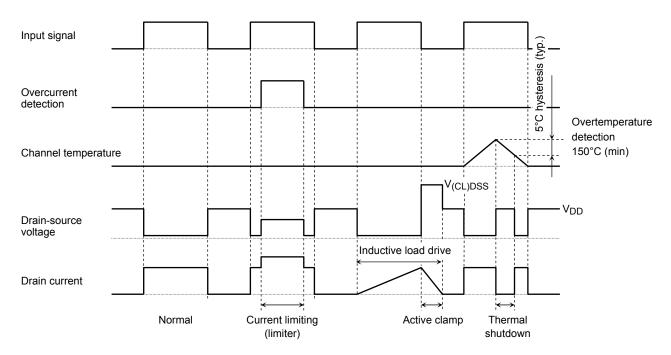
Block Diagram



Pin Description

Pin No.	Symbol	Pin Description				
1	SOURCE1	Source pin 1.				
	IN1	Input pin 1.				
2		This pin is connected to a pull-down resistor internally, so that even if the input is open-circuited, output never turns on inadvertently.				
3	SOURCE2	Source pin 2.				
	IN2	Input pin 2.				
4		This pin is connected to a pull-down resistor internally, so that even if the input is open-circuited, output never turns on inadvertently.				
E G	DRAIN2	Drain pin 2.				
5, 6		Drain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.				
7 0	DRAIN1	Drain pin 1.				
7, 8		Drain current is limited (by current limiter) if it exceeds 1 A (min) in order to protect the IC.				

Timing Chart



Truth Table

V _{IN}	V _{DS}	Output State	Operating State
L	Н	Off	Normal
Н	L	On	Normai
L	Н	Off	
н	н	Current limiting (limiter)	Load short-circuited
L	н	Off	Overtemperature
Н	Н	Off	Overtemperature

Absolute Maximum Ratings (Ta = 25°C)

Characterist	Symbol	Rating	Unit	
Drain-source voltage	DC	V _{DS}	30	V
Drain current	I _D	Internally limited	А	
Input voltage	V _{IN}	-0.3 to 6	V	
Power dissipation (t = 10 s) (Not	PD	2.0	W	
Single pulse active clamp capabili	E _{AS}	23	mJ	
Active clamp current	I _{AR}	1.5	А	
Repetitive active clamp capability	E _{AR}	E _{AR} 0.2		
Operating temperature	T _{opr}	-40 to 110	°C	
Channel temperature		T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to 150	°C	

Note 1: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (Note 2)	R _{th (ch-a)}	62.5	°C/W

Note 2: Mount on glass epoxy boad [$25.4 \times 25.4 \times 0.8$ mm] (with the two devices driving)(t =10 s)

Note 3: Single pulse active clamp capability test condition V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 10 mH, I_{AR} = 1.5 A, R_G = 25 Ω

Note 4: Repetitive rating: Pulse width limited by maximum channel temperature

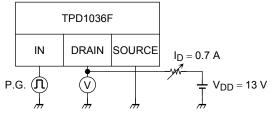
Electrical Characteristics

Characteristics	Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Drain-source clamp voltage	V _{(CL)DSS}		T _{ch} = -40 to 110°C	$V_{IN} = 0 V, I_D = 1mA$	40	_	60	V
Input threshold voltage	V _{th}	_	T _{ch} = 25°C	V _{DS} = 13 V, I _D = 10mA	1.0	_	2.8	v
			T _{ch} = -40 to 110°C		0.9	_	3.0	
Protective circuit operation	Maria		T _{ch} = 25°C	—	3		6	v
input voltage range	V _{IN (opr)}		T _{ch} = -40 to 110°C	—	3.5		6	
Drain cut-off current	IDSS	_	T _{ch} = 25°C	V _{IN} = 0 V, V _{DS} = 30V			10	μA
			T _{ch} = -40 to 110°C				100	
	I _{IN (1)}	_	T _{ch} = -40 to 110°C	$V_{IN} = 5 V$, at normal operation	_		300	μA
Input current	I _{IN (2)}		T _{ch} = -40 to 110°C	V _{IN} = 5 V, when overcurrent protective circuit is actuated			350	
Drain-source ON-resistance	R _{DS (ON)}	_	T _{ch} = 25°C	V _{IN} = 5 V, I _D = 0.7 A		0.3	0.5	Ω
			T _{ch} = -40 to 110°C				0.75	
Overtemperature detection	Τ _S			$V_{IN} = 5 V$	150	160		°C
Overcurrent detection	IS	2	T _{ch} = 25°C	V _{IN} = 5 V	1.5	2.5		A
		2	T _{ch} = -40 to 110°C		1			
	t _{ON}		T _{ch} = 25°C	V _{DD} = 13 V, V _{IN} = 0 V/5 V, I _D = 0.7 A			30	μs
Switching times		- 1	T _{ch} = -40 to 110°C				60	
Switching times	tOFF		T _{ch} = 25°C				60	
			T _{ch} = -40 to 110°C				90	
Drain-source diode forward voltage	V _{DSF}		T _{ch} = 25°C	$V_{IN} = 0 V$, $I_F = 1.5 A$		_	1.7	V

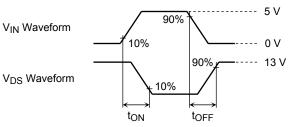
Test Circuit 1

Switching times measuring circuit

Test Circuit



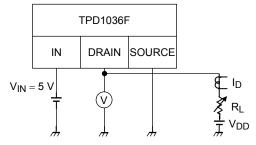
Measured Waveforms

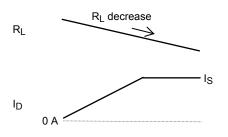


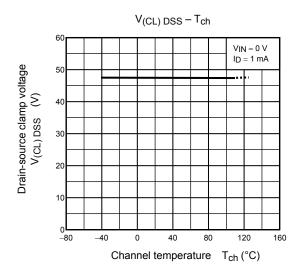
Test Circuit 2

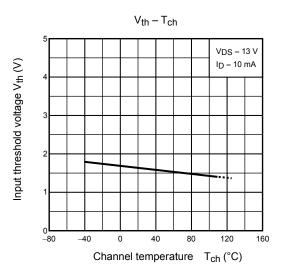
Overcurrent detection measuring circuit

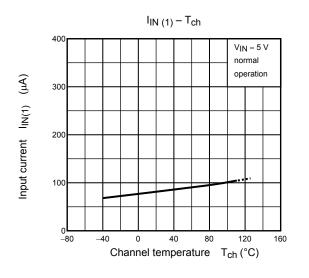
Test Circuit

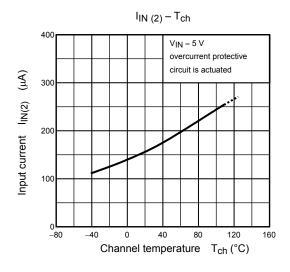


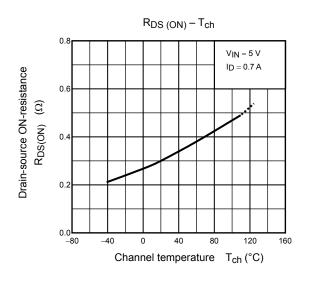


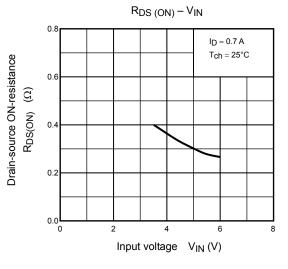


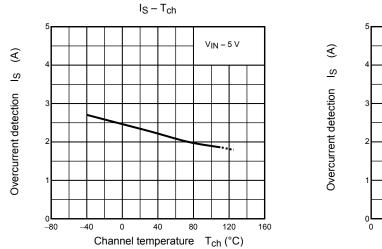


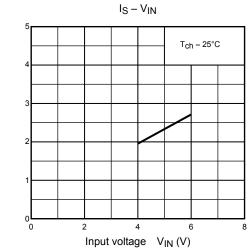


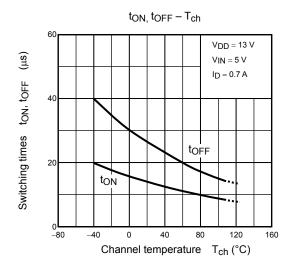




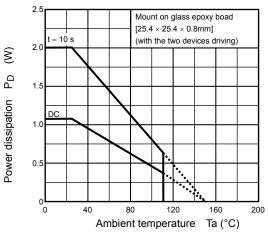






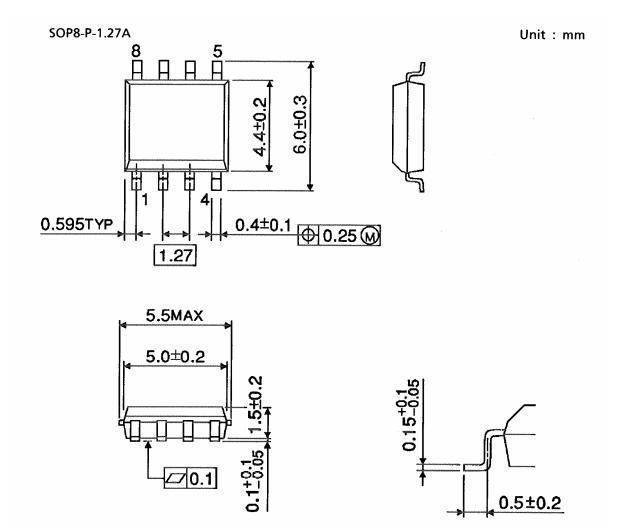






<u>TOSHIBA</u>

Package Dimensions



Weight: 0.08 g (typ.)

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20070701-EN GENERAL

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